

Description

The SXG110N10NF uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 100V$ $I_D = 110A$

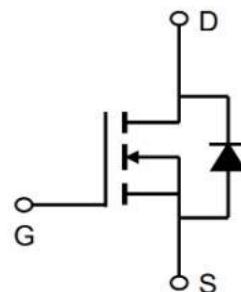
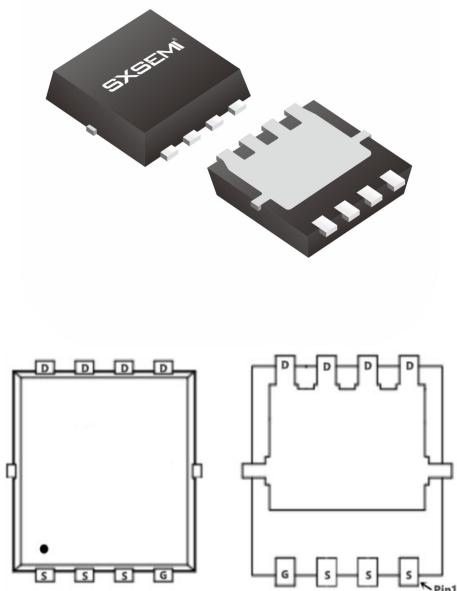
$R_{DS(ON)} < 6m\Omega$ @ $V_{GS}=10V$

Application

DC/DC Converter

LED Backlighting

Power Management Switches

PDFN5*6-8L**Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Value	Unit
V_{DS}	Drain source voltage	100	V
V_{GS}	Gate source voltage	± 20	V
I_D	Continuous drain current, $TC=25^\circ C$	110	A
IDM	Pulsed drain current, $TC=25^\circ C$	380	A
PD	Power dissipation, $TC=25^\circ C$	113.6	W
EAS	Single pulsed avalanche energy ⁴⁾	205	mJ
T_{stg}, T_j	Operation and storage temperature	-55 to 150	°C
$R_{\theta JC}$	Thermal resistance, junction-case	1.1	°C/W
$R_{\theta JA}$	Thermal resistance, junction-ambient ⁴⁾	58	°C/W

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
VDSS	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	100	-	-	V
IGSS	Gate-body Leakage current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
IDSS	Zero Gate Voltage Drain Current $T_J=25^\circ\text{C}$	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
IDSS	Zero Gate Voltage Drain Current $T_J=100^\circ\text{C}$		-	-	100	
VGS(th)	Gate-Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.2	1.8	2.5	V
RDS(on)	Drain-Source on-Resistance ²	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	-	4.2	6	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 15\text{A}$	-	6.6	9	
Ciss	Input Capacitance	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	-	4400	-	pF
Coss	Output Capacitance		-	645	-	
Crss	Reverse Transfer Capacitance		-	20	-	
Rg	Gate Resistance	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$	-	1.7	-	Ω
Qg	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}, I_D = 20\text{A}$	-	75	-	nC
Qgs	Gate-Source Charge		-	17	-	
Qgd	Gate-Drain Charge		-	13	-	
td(on)	Turn-on Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}, R_G = 3\Omega, I_D = 20\text{A}$	-	15.4	-	ns
tr	Rise Time		-	13	-	
td(off)	Turn-off Delay Time		-	34	-	
tf	Fall Time		-	6.2	-	
VSD	Diode Forward Voltage ²	$I_F = 20\text{A}, V_{GS} = 0\text{V}$	-	-	1.2	V
IS	Continuous Source Current ^{1,5}	$V_G = V_D = 0\text{V}$, Force Current	-	-	95	A
trr	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, dI/dt = 100\text{A}/\mu\text{s}$	-	55	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	101	-	nC

Notes:

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $V_{DD}=50\text{V}$, $V_{GS}=10\text{V}$, $L=0.4\text{mH}$, $I_{AS}=32\text{A}$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_D and I_{Dm} , in real applications , should be limited by total power dissipation.

Typical Characteristics

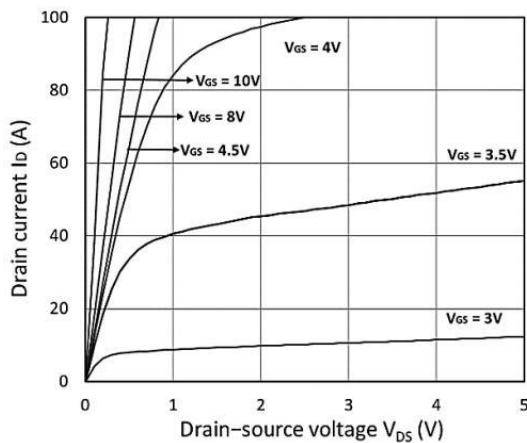


Figure 1. Output Characteristics

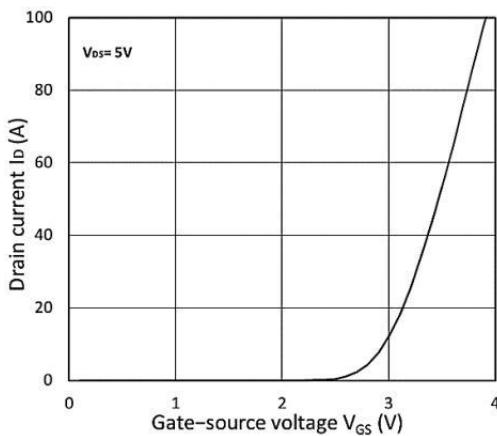


Figure 2. Transfer Characteristics

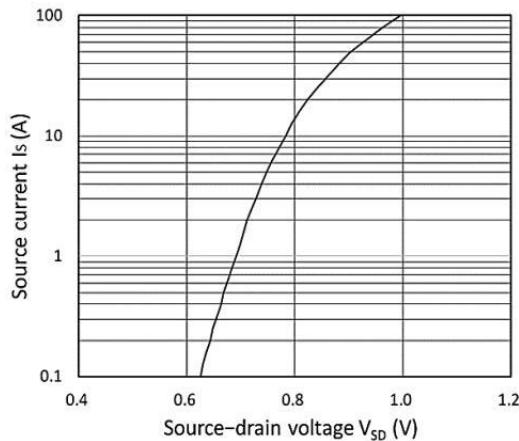


Figure 3. Forward Characteristics of Reverse

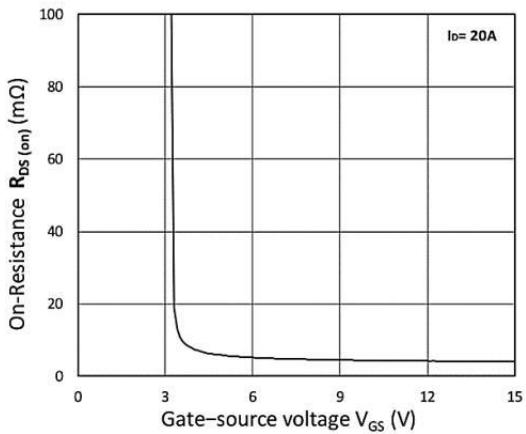


Figure 4. RDS(ON) vs. VGS

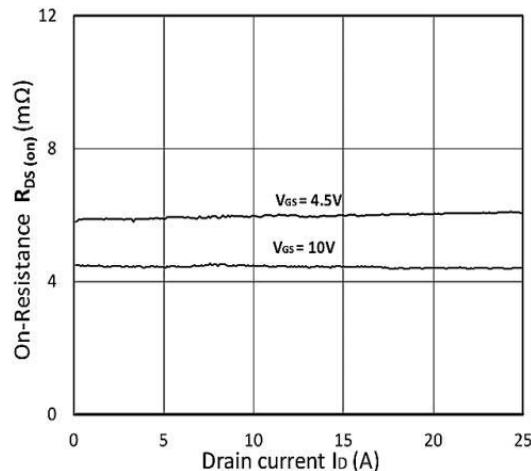


Figure 5. R DS(ON) vs. ID

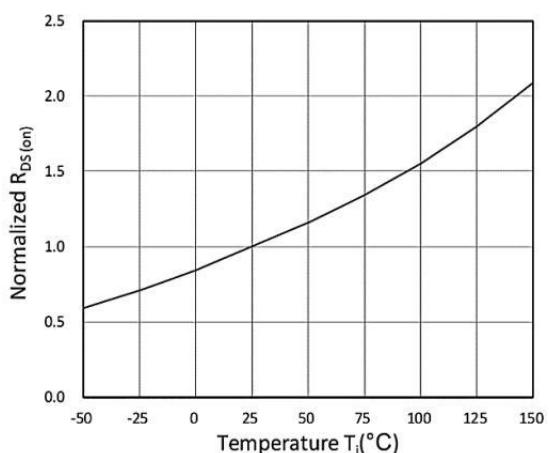


Figure 6. Normalized R DS(ON) vs. Temperature

Typical Characteristics

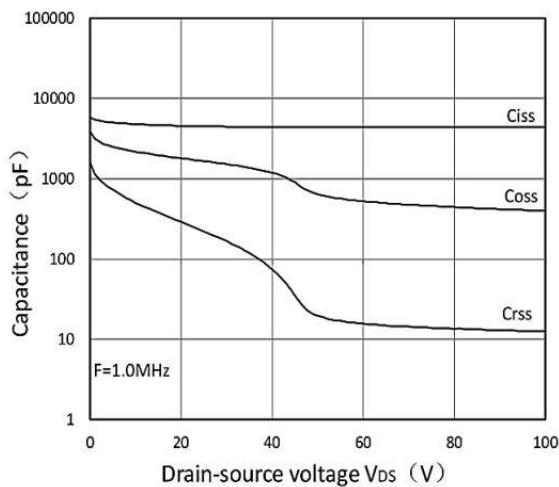


Figure 7. Capacitance Characteristics

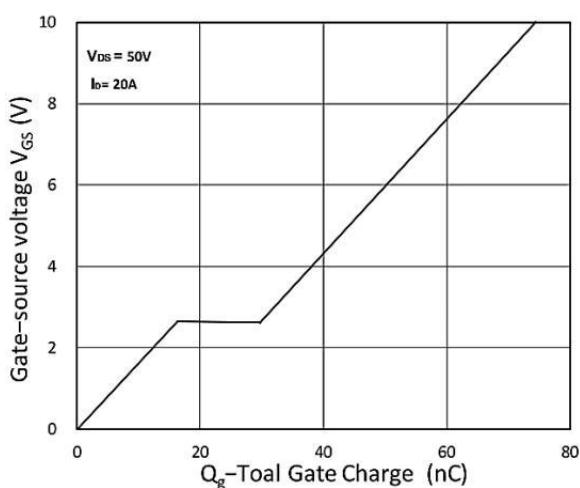


Figure 8. Gate Charge Characteristics

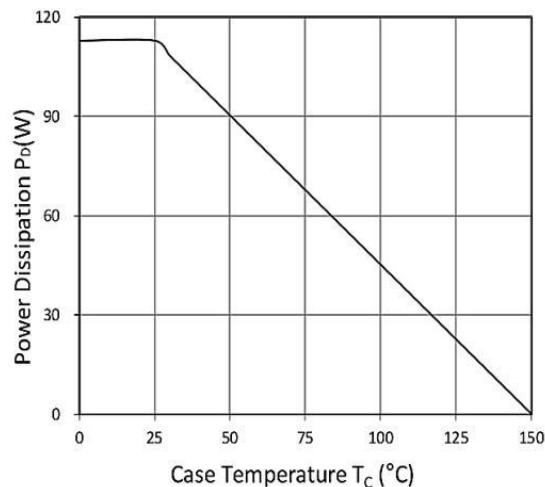


Figure 9. Power Dissipation

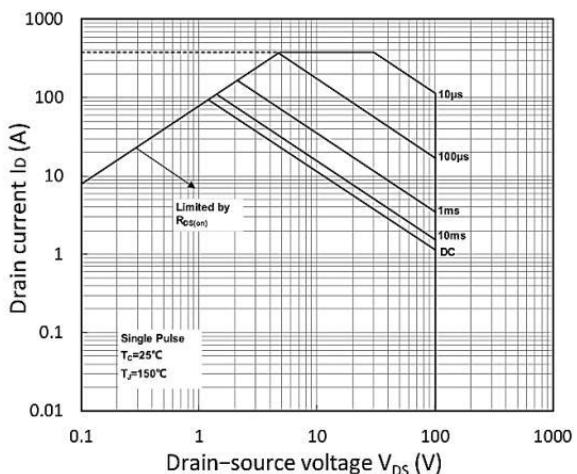


Figure 10. Safe Operating Area

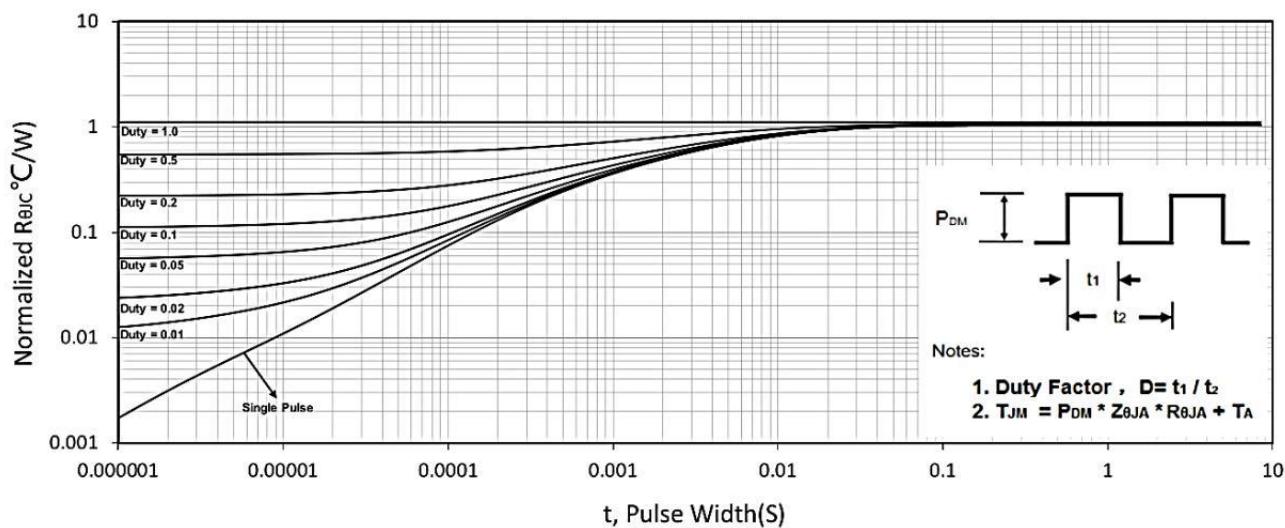
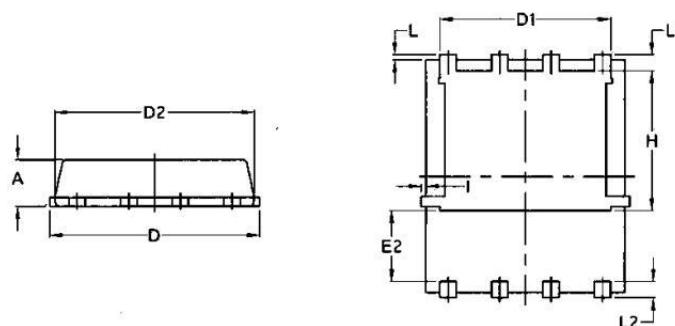
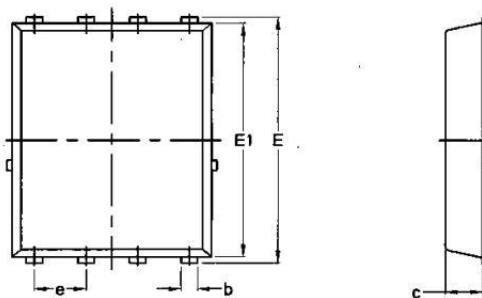


Figure 11. Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-PDFN5*6-8L-JQ Single

Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000